



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:

NISHIMOTO et al

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Art Unit: 2823

Serial No.: 08/897,839

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Examiner: K. Eaton

Filed: July 21, 1997

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For: STRESS-ADJUSTED INSULATING
FILM FORMING METHOD,
SEMICONDUCTOR DEVICE AND
METHOD OF MANUFACTURING THE
SAME

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)
)

RESPONSE TO OFFICE ACTION OF MARCH 20, 2001

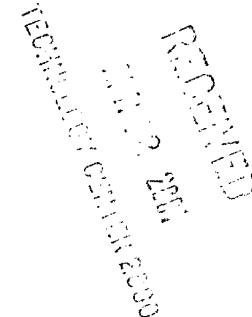
Assistant Commissioner for Patents
Washington, D.C. 20231

Sir:

Responsive to the office action of March 20, 2001, applicants, by their undersigned attorney, hereby elect claims 43-48 (Group I) with traverse.

The restriction requirement is traversed for the reason that the alternative method hypothesized by the examiner for forming the semiconductor device of Group II is impractical. The examiner's hypothetical method requires provision of a self-supporting "interconnection layer" to which a substrate with a "first insulating film" is laminated. Given the conventional thickness of a conductive interconnection layer, lamination of such a "conductive interconnection layer" to a substrate would be impractical if not impossible, even if the conventional thin films could be made self-supporting. For the foregoing reasons, the examiner has not hypothesized a

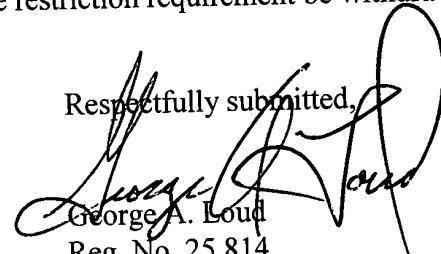
2823
26/Election
whereas
4-13-01



realistic alternative method for producing the product defined by the claims of Group II.

Accordingly, it is respectfully requested that the restriction requirement be withdrawn.

Respectfully submitted,


George A. Loud
Reg. No. 25,814

Dated: April 11, 2001

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